SDB310WS

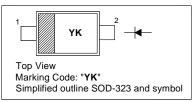
SCHOTTKY BARRIER DIODE

Features

- Low power rectified
- Silicon epitaxial type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I _F	0.2	А
Repetitive Peak Forward Current	I _{FRM}	0.5	А
Non-Repetitive Peak Forward Current (8.3 ms)	I _{FSM}	1	А
Power Dissipation	P _D	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$ at $I_F = 30 \text{ mA}$	V _F	0.4 0.5	V
Reverse Current at $V_R = 30 \text{ V}$	I _R	1	μΑ
Total Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	Ст	10	pF

SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 10/03/2008

Fig. 1 I_F - V_F

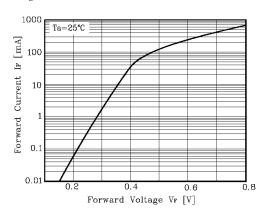


Fig. 2 I_R - V_R

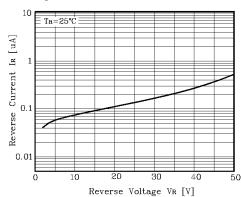
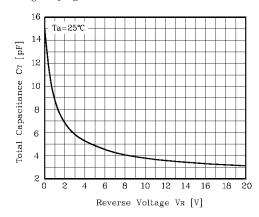


Fig. 3 C_T - V_R





SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)





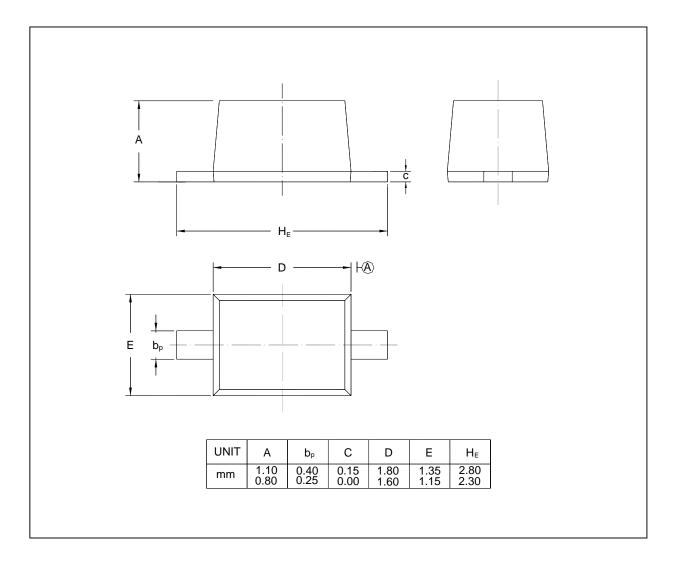


Dated: 10/03/2008

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323





SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 10/03/2008